



APPLICATION DATA SHEET

Electronic Version v14

Stylesheet Version v14.0

Title of Invention	METHOD OF FORMING HIGH VOLTAGE METAL OXIDE SEMICONDUCTOR TRANSISTOR		
Application Type : regular, utility Attorney Docket Number : NAUP0531USA			
Correspondence address: Customer Number: 027765			
			
Inventor Information: <u>Inventor 1:</u> Applicant Authority Type: Inventor Citizenship: TW Given Name: Chin-Long Family Name: Chen Residence: City of Residence: Hsin-Chu Hsien Country of Residence: TW Address-1 of Mailing Address: No. 438, Tien-Hsin Sub-Ward, Hsin-Pu Town Address-2 of Mailing Address: City of Mailing Address: Hsin-Chu Hsien State of Mailing Address: Postal Code of Mailing Address: Country of Mailing Address: TW Phone: Fax: E-mail:			
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 as my attorney(s) or agent(s) to prosecute the application identified above, and to transact all business in the United States Patent and Trademark Office connected therewith.			